



IRFI530NPBF Information



For Reference Only

Part Number IRFI530NPBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 12A TO220FP

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFI530NPBF Specifications

Manufacturer Part Number IRF1530NPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack		
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Package TO-220-3 Full Pack Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 640pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Manufacturer	Infineon Technologies
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack	Package	TO-220-3 Full Pack
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack	Series	HEXFET?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature Supplier Device Package TO-220AB Full-Pak Package / Case 12A (Tc) 140	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds640pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 640pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Current - Continuous Drain (Id) @ 25°C	12A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 640pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)41W (Tc)Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	44nC @ 10V
FET Feature - Power Dissipation (Max) 41W (Tc) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	640pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 110 mOhm @ 6.6A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs110 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB Full-PakPackage / CaseTO-220-3 Full Pack	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	41W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	110 mOhm @ 6.6A, 10V
Supplier Device Package TO-220AB Full-Pak Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB Full-Pak
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

IRFI530NPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFI530NPBF Payment Methods





















IRFI530NPBF Shipping Methods













If you have any question about IRFI530NPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com